Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

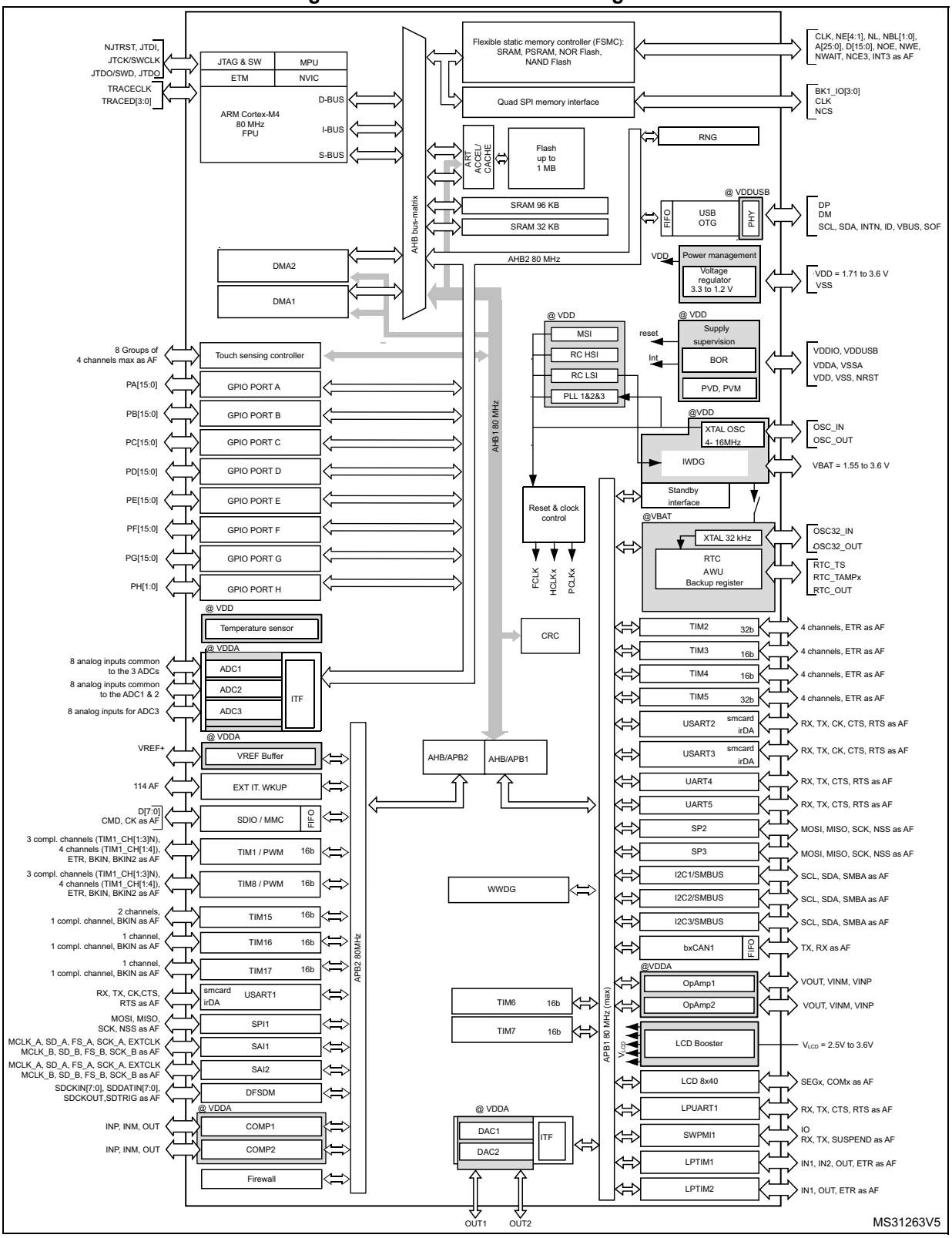
Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	51
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l476rgt6tr

Table 2. STM32L476xx family device features and peripheral counts (continued)

Peripheral	STM32L476 Zx	STM32L476 Qx	STM32L476 Vx	STM32L476 Mx	STM32L476 Jx	STM32L476 Rx
Max. CPU frequency	80 MHz					
Operating voltage	1.71 to 3.6 V					
Operating temperature	Ambient operating temperature: -40 to 85 °C / -40 to 105 °C / -40 to 125 °C Junction temperature: -40 to 105 °C / -40 to 125 °C / -40 to 130 °C					
Packages	LQFP144	UFBGA132	LQFP100	WLCSP81	WLCSP72	LQFP64

1. For the LQFP100 package, only FMC Bank1 is available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select.

Figure 1. STM32L476xx block diagram



Note: AF: alternate function on I/O pins.

3.4 Embedded Flash memory

STM32L476xx devices feature up to 1 Mbyte of embedded Flash memory available for storing programs and data. The Flash memory is divided into two banks allowing read-while-write operations. This feature allows to perform a read operation from one bank while an erase or program operation is performed to the other bank. The dual bank boot is also supported. Each bank contains 256 pages of 2 Kbyte.

Flexible protections can be configured thanks to option bytes:

- Readout protection (RDP) to protect the whole memory. Three levels are available:
  - Level 0: no readout protection
  - Level 1: memory readout protection: the Flash memory cannot be read from or written to if either debug features are connected, boot in RAM or bootloader is selected
  - Level 2: chip readout protection: debug features (Cortex-M4 JTAG and serial wire), boot in RAM and bootloader selection are disabled (JTAG fuse). This selection is irreversible.

Table 3. Access status versus readout protection level and execution modes

Area	Protection level	User execution			Debug, boot from RAM or boot from system memory (loader)		
		Read	Write	Erase	Read	Write	Erase
Main memory	1	Yes	Yes	Yes	No	No	No
	2	Yes	Yes	Yes	N/A	N/A	N/A
System memory	1	Yes	No	No	Yes	No	No
	2	Yes	No	No	N/A	N/A	N/A
Option bytes	1	Yes	Yes	Yes	Yes	Yes	Yes
	2	Yes	No	No	N/A	N/A	N/A
Backup registers	1	Yes	Yes	N/A(1)	No	No	N/A(1)
	2	Yes	Yes	N/A	N/A	N/A	N/A
SRAM2	1	Yes	Yes	Yes(1)	No	No	No(1)
	2	Yes	Yes	Yes	N/A	N/A	N/A

1. Erased when RDP change from Level 1 to Level 0.

- Write protection (WRP): the protected area is protected against erasing and programming. Two areas per bank can be selected, with 2-Kbyte granularity.
- Proprietary code readout protection (PCROP): a part of the flash memory can be protected against read and write from third parties. The protected area is execute-only: it can only be reached by the STM32 CPU, as an instruction code, while all other accesses (DMA, debug and CPU data read, write and erase) are strictly prohibited. One area per bank can be selected, with 64-bit granularity. An additional option bit (PCROP_RDP) allows to select if the PCROP area is erased or not when the RDP protection is changed from Level 1 to Level 0.

3.9.3 Voltage regulator

Two embedded linear voltage regulators supply most of the digital circuitries: the main regulator (MR) and the low-power regulator (LPR).

- The MR is used in the Run and Sleep modes and in the Stop 0 mode.
- The LPR is used in Low-Power Run, Low-Power Sleep, Stop 1 and Stop 2 modes. It is also used to supply the 32 Kbyte SRAM2 in Standby with RAM2 retention.
- Both regulators are in power-down in Standby and Shutdown modes: the regulator output is in high impedance, and the kernel circuitry is powered down thus inducing zero consumption.

The ultralow-power STM32L476xx supports dynamic voltage scaling to optimize its power consumption in run mode. The voltage from the Main Regulator that supplies the logic (VCORE) can be adjusted according to the system's maximum operating frequency.

There are two power consumption ranges:

- Range 1 with the CPU running at up to 80 MHz.
- Range 2 with a maximum CPU frequency of 26 MHz. All peripheral clocks are also limited to 26 MHz.

The VCORE can be supplied by the low-power regulator, the main regulator being switched off. The system is then in Low-power run mode.

- Low-power run mode with the CPU running at up to 2 MHz. Peripherals with independent clock can be clocked by HSI16.

3.9.4 Low-power modes

The ultra-low-power STM32L476xx supports seven low-power modes to achieve the best compromise between low-power consumption, short startup time, available peripherals and available wakeup sources:

3.11 Clocks and startup

The clock controller (see *Figure 3*) distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low-power modes and ensures clock robustness. It features:

- **Clock prescaler:** to get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler
- **Safe clock switching:** clock sources can be changed safely on the fly in run mode through a configuration register.
- **Clock management:** to reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.
- **System clock source:** four different clock sources can be used to drive the master clock SYSCLK:
  - 4-48 MHz high-speed external crystal or ceramic resonator (HSE), that can supply a PLL. The HSE can also be configured in bypass mode for an external clock.
  - 16 MHz high-speed internal RC oscillator (HSI16), trimmable by software, that can supply a PLL
  - Multispeed internal RC oscillator (MSI), trimmable by software, able to generate 12 frequencies from 100 kHz to 48 MHz. When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be automatically trimmed by hardware to reach better than ±0.25% accuracy. In this mode the MSI can feed the USB device, saving the need of an external high-speed crystal (HSE). The MSI can supply a PLL.
  - System PLL which can be fed by HSE, HSI16 or MSI, with a maximum frequency at 80 MHz.
- **Auxiliary clock source:** two ultralow-power clock sources that can be used to drive the LCD controller and the real-time clock:
  - 32.768 kHz low-speed external crystal (LSE), supporting four drive capability modes. The LSE can also be configured in bypass mode for an external clock.
  - 32 kHz low-speed internal RC (LSI), also used to drive the independent watchdog. The LSI clock accuracy is ±5% accuracy.
- **Peripheral clock sources:** Several peripherals (USB, SDMMC, RNG, SAI, USARTs, I2Cs, LPTimers, ADC, SWPMI) have their own independent clock whatever the system clock. Three PLLs, each having three independent outputs allowing the highest flexibility, can generate independent clocks for the ADC, the USB/SDMMC/RNG and the two SAIs.
- **Startup clock:** after reset, the microcontroller restarts by default with an internal 4 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.
- **Clock security system (CSS):** this feature can be enabled by software. If a HSE clock failure occurs, the master clock is automatically switched to HSI16 and a software

Many features are shared with those of the general-purpose TIMx timers (described in *Section 3.24.2*) using the same architecture, so the advanced-control timers can work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

3.24.2 General-purpose timers (TIM2, TIM3, TIM4, TIM5, TIM15, TIM16, TIM17)

There are up to seven synchronizable general-purpose timers embedded in the STM32L476 (see *Table 10* for differences). Each general-purpose timer can be used to generate PWM outputs, or act as a simple time base.

- TIM2, TIM3, TIM4 and TIM5

  They are full-featured general-purpose timers:

  – TIM2 and TIM5 have a 32-bit auto-reload up/downcounter and 32-bit prescaler

  – TIM3 and TIM4 have 16-bit auto-reload up/downcounter and 16-bit prescaler.

  These timers feature 4 independent channels for input capture/output compare, PWM or one-pulse mode output. They can work together, or with the other general-purpose timers via the Timer Link feature for synchronization or event chaining.

  The counters can be frozen in debug mode.

  All have independent DMA request generation and support quadrature encoders.

- TIM15, 16 and 17

  They are general-purpose timers with mid-range features:

  They have 16-bit auto-reload upcounters and 16-bit prescalers.

  – TIM15 has 2 channels and 1 complementary channel

  – TIM16 and TIM17 have 1 channel and 1 complementary channel

  All channels can be used for input capture/output compare, PWM or one-pulse mode output.

  The timers can work together via the Timer Link feature for synchronization or event chaining. The timers have independent DMA request generation.

  The counters can be frozen in debug mode.

3.24.3 Basic timers (TIM6 and TIM7)

The basic timers are mainly used for DAC trigger generation. They can also be used as generic 16-bit timebases.

3.24.4 Low-power timer (LPTIM1 and LPTIM2)

The devices embed two low-power timers. These timers have an independent clock and are running in Stop mode if they are clocked by LSE, LSI or an external clock. They are able to wakeup the system from Stop mode.

LPTIM1 is active in Stop 0, Stop 1 and Stop 2 modes.

LPTIM2 is active in Stop 0 and Stop 1 mode.

Table 13. SAI implementation

SAI features(1)	SAI1	SAI2
I2S, LSB or MSB-justified, PCM/DSP, TDM, AC'97	X	X
Mute mode	X	X
Stereo/Mono audio frame capability.	X	X
16 slots	X	X
Data size configurable: 8-, 10-, 16-, 20-, 24-, 32-bit	X	X
FIFO Size	X (8 Word)	X (8 Word)
SPDIF	X	X

1. X: supported

3.31 Single wire protocol master interface (SWPMI)

The Single wire protocol master interface (SWPMI) is the master interface corresponding to the Contactless Frontend (CLF) defined in the ETSI TS 102 613 technical specification. The main features are:

- full-duplex communication mode
- automatic SWP bus state management (active, suspend, resume)
- configurable bitrate up to 2 Mbit/s
- automatic SOF, EOF and CRC handling

SWPMI can be served by the DMA controller.

3.32 Controller area network (CAN)

The CAN is compliant with specifications 2.0A and B (active) with a bit rate up to 1 Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. It has three transmit mailboxes, two receive FIFOs with 3 stages and 14 scalable filter banks.

The CAN peripheral supports:

- Supports CAN protocol version 2.0 A, B Active
- Bit rates up to 1 Mbit/s

Table 15. STM32L476xxSTM32L476xx pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP72	WLCSP81	LQFP100	UFBGA132	LQFP144					Alternate functions	Additional functions
-	-	-	20	-	31	VREF-	S	-	-	-	-
12	G9	G9	-	J1	-	VSSA/VREF-	-	-	-	-	-
-	G8	G8	21	L1	32	VREF+	S	-	-	-	VREFBUF_OUT
-	H9	H9	22	M1	33	VDDA	S	-	-	-	-
13	-	-	-	-	-	VDDA/VREF+	S	-	-	-	-
14	H8	H8	23	L2	34	PA0	I/O	FT_a	-	TIM2_CH1, TIM5_CH1, TIM8_ETR, USART2_CTS, UART4_TX, SAI1_EXTCLK, TIM2_ETR, EVENTOUT	OPAMP1_VINP, ADC12_IN5, RTC_TAMP2/WKUP1
-	-	-	-	M3	-	OPAMP1_VINM	I	TT	-	-	-
15	G4	G4	24	M2	35	PA1	I/O	FT_la	-	TIM2_CH2, TIM5_CH2, USART2_RTS_DE, UART4_RX, LCD_SEG0, TIM15_CH1N, EVENTOUT	OPAMP1_VINM, ADC12_IN6
16	G6	G6	25	K3	36	PA2	I/O	FT_la	-	TIM2_CH3, TIM5_CH3, USART2_TX, LCD_SEG1, SAI2_EXTCLK, TIM15_CH1, EVENTOUT	ADC12_IN7, WKUP4/LSCO
17	H7	H7	26	L3	37	PA3	I/O	TT	-	TIM2_CH4, TIM5_CH4, USART2_RX, LCD_SEG2, TIM15_CH2, EVENTOUT	OPAMP1_VOUT, ADC12_IN8
18	J9	J9	27	E3	38	VSS	S	-	-	-	-
19	J8	J8	28	H3	39	VDD	S	-	-	-	-
20	G5	G5	29	J4	40	PA4	I/O	TT_a	-	SPI1_NSS, SPI3_NSS, USART2_CK, SAI1_FS_B, LPTIM2_OUT, EVENTOUT	ADC12_IN9, DAC1_OUT1
21	H6	H6	30	K4	41	PA5	I/O	TT_a	-	TIM2_CH1, TIM2_ETR, TIM8_CH1N, SPI1_SCK, LPTIM2_ETR, EVENTOUT	ADC12_IN10, DAC1_OUT2
22	H5	H5	31	L4	42	PA6	I/O	FT_la	-	TIM1_BKIN, TIM3_CH1, TIM8_BKIN, SPI1_MISO, USART3_CTS, QUADSPI_BK1_IO3, LCD_SEG3, TIM1_BKIN_COMP2, TIM8_BKIN_COMP2, TIM16_CH1, EVENTOUT	OPAMP2_VINP, ADC12_IN11

Table 15. STM32L476xxSTM32L476xx pin definitions (continued)

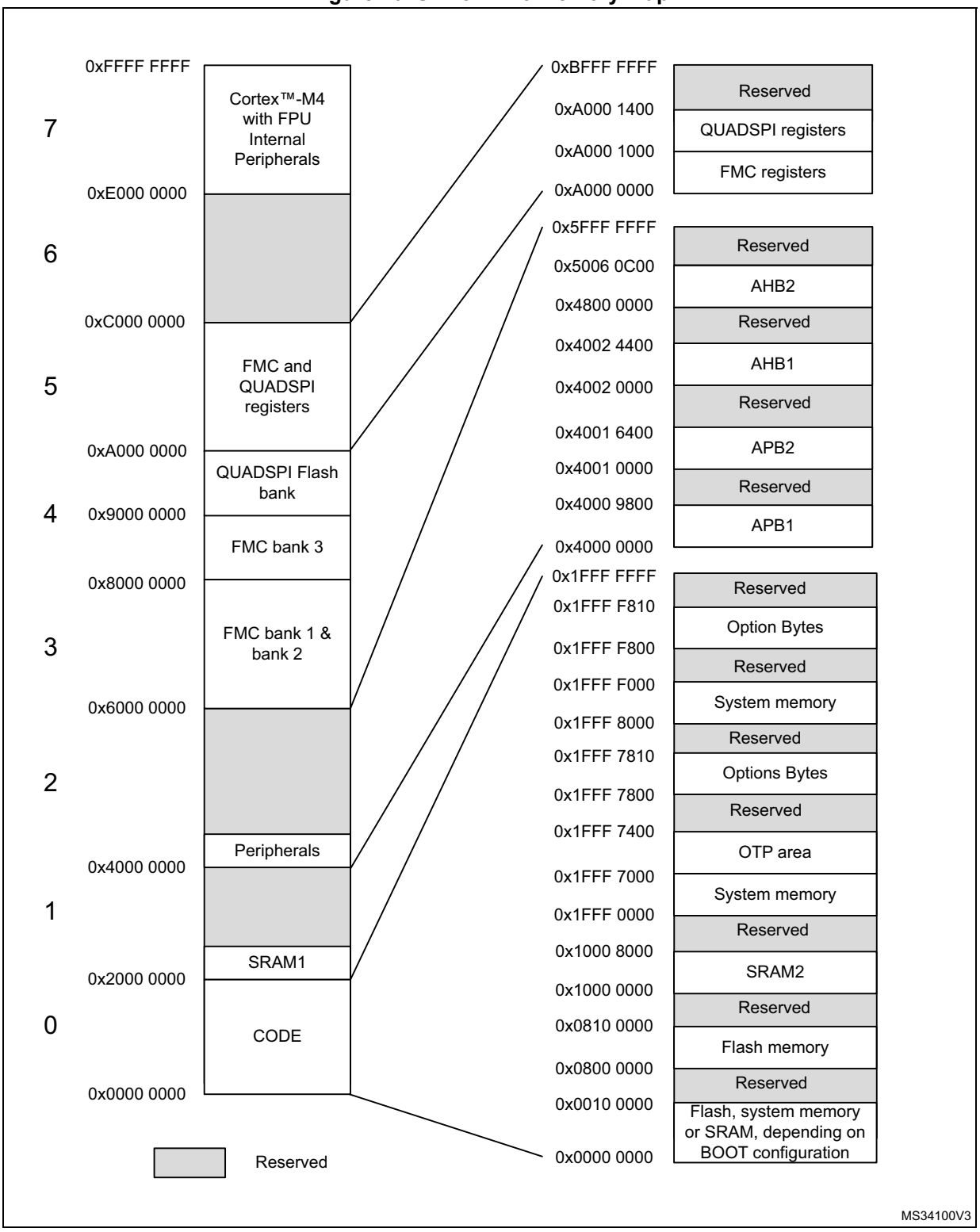
Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP72	WLCSP81	LQFP100	UFBGA132	LQFP144					Alternate functions	Additional functions
-	-	-	82	B9	115	PD1	I/O	FT	-	SPI2_SCK, DFSDM_CKIN7, CAN1_TX, FMC_D3, EVENTOUT	-
54	A3	A3	83	C8	116	PD2	I/O	FT_l	-	TIM3_ETR, USART3_RTS_DE, UART5_RX, TSC_SYNC, LCD_COM7/LCD_SEG31/ LCD_SEG43, SDMMC1_CMD, EVENTOUT	-
-	-	-	84	B8	117	PD3	I/O	FT	-	SPI2_MISO, DFSDM_DATIN0, USART2_CTS, FMC_CLK, EVENTOUT	-
-	-	E5	85	B7	118	PD4	I/O	FT	-	SPI2_MOSI, DFSDM_CKIN0, USART2_RTS_DE, FMC_NOE, EVENTOUT	-
-	-	D4	86	A6	119	PD5	I/O	FT	-	USART2_TX, FMC_NWE, EVENTOUT	-
-	-	-	-	-	120	VSS	S	-	-	-	-
-	-	E4	-	-	121	VDD	S	-	-	-	-
-	-	D5	87	B6	122	PD6	I/O	FT	-	DFSDM_DATIN1, USART2_RX, FMC_NWAIT, SAI1_SD_A, EVENTOUT	-
-	-	D6	88	A5	123	PD7	I/O	FT	-	DFSDM_CKIN1, USART2_CK, FMC_NE1, EVENTOUT	-
-	A4	A4	-	D9	124	PG9	I/O	FT_s	-	SPI3_SCK, USART1_TX, FMC_NCE3/FMC_NE2, SAI2_SCK_A, TIM15_CH1N, EVENTOUT	-
-	B4	B4	-	D8	125	PG10	I/O	FT_s	-	LPTIM1_IN1, SPI3_MISO, USART1_RX, FMC_NE3, SAI2_FS_A, TIM15_CH1, EVENTOUT	-
-	C4	C4	-	G3	126	PG11	I/O	FT_s	-	LPTIM1_IN2, SPI3_MOSI, USART1_CTS, SAI2_MCLK_A, TIM15_CH2, EVENTOUT	-

Table 16. Alternate function AF0 to AF7 (for AF8 to AF15 see *Table 17*) (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SYS_AF	TIM1/TIM2/ TIM5/TIM8/ LPTIM1	TIM1/TIM2/ TIM3/TIM4/ TIM5	TIM8	I2C1/I2C2/I2C3	SPI1/SPI2	SPI3/DFSDM	USART1/ USART2/ USART3
Port E	PE0	-	-	TIM4_ETR	-	-	-	-	-
	PE1	-	-	-	-	-	-	-	-
	PE2	TRACECK	-	TIM3_ETR	-	-	-	-	-
	PE3	TRACED0	-	TIM3_CH1	-	-	-	-	-
	PE4	TRACED1	-	TIM3_CH2	-	-	-	DFSDM_DATIN3	-
	PE5	TRACED2	-	TIM3_CH3	-	-	-	DFSDM_CKIN3	-
	PE6	TRACED3	-	TIM3_CH4	-	-	-	-	-
	PE7	-	TIM1_ETR	-	-	-	-	DFSDM_DATIN2	-
	PE8	-	TIM1_CH1N	-	-	-	-	DFSDM_CKIN2	-
	PE9	-	TIM1_CH1	-	-	-	-	DFSDM_CKOUT	-
	PE10	-	TIM1_CH2N	-	-	-	-	DFSDM_DATIN4	-
	PE11	-	TIM1_CH2	-	-	-	-	DFSDM_CKIN4	-
	PE12	-	TIM1_CH3N	-	-	-	SPI1_NSS	DFSDM_DATIN5	-
	PE13	-	TIM1_CH3	-	-	-	SPI1_SCK	DFSDM_CKIN5	-
	PE14	-	TIM1_CH4	TIM1_BKIN2	TIM1_BKIN2_ COMP2	-	SPI1_MISO	-	-
	PE15	-	TIM1_BKIN	-	TIM1_BKIN_ COMP1	-	SPI1_MOSI	-	-

5 Memory mapping

Figure 10. STM32L476 memory map



6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 53*. They are based on the EMS levels and classes defined in application note AN1709.

Table 53. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{HCLK} = 80 MHz, conforming to IEC 61000-4-2	3B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{HCLK} = 80 MHz, conforming to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Table 58. I/O static characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{lkg}	FT_xx input leakage current(3)	$V_{IN} \le Max(V_{DDXXX})$(4)	-	-	±100	nA
		$Max(V_{DDXXX}) \le V_{IN} \le Max(V_{DDXXX})+1$ V(4)(5)	-	-	650(3)(6)	
		$Max(V_{DDXXX})+1$ V < VIN ≤ 5.5 V(3)(5)	-	-	200(6)	
	FT_lu, FT_u and PC3 IO	$V_{IN} \le Max(V_{DDXXX})$ (4)	-	-	±150	
		$Max(V_{DDXXX}) \le V_{IN} \le Max(V_{DDXXX})+1$ V(4)	-	-	2500(3)(7)	
		$Max(V_{DDXXX})+1$ V < VIN ≤ 5.5 V(4)(5)(7)	-	-	250(7)	
	TT_xx input leakage current	$V_{IN} \le Max(V_{DDXXX})$(6)	-	-	±150	
		$Max(V_{DDXXX}) \le V_{IN}$ < 3.6 V(6)	-	-	2000(3)	
	OPAMPx_VINM (x=1,2) dedicated input leakage current (UFBGA132 only)	T_J = 75 °C	-	-	1	
R_{PU}	Weak pull-up equivalent resistor (8)	$V_{IN} = V_{SS}$	25	40	55	kΩ
R_{PD}	Weak pull-down equivalent resistor(8)	$V_{IN} = V_{DDIOx}$	25	40	55	kΩ
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. Refer to *Figure 22: I/O input characteristics*.
2. Tested in production.
3. Guaranteed by design.
4. $Max(V_{DDXXX})$ is the maximum value of all the I/O supplies. Refer to *Table: Legend/Abbreviations used in the pinout table.*
5. All TX_xx IO except FT_lu, FT_u and PC3.
6. This value represents the pad leakage of the IO itself. The total product pad leakage is provided by this formula: $I_{Total\_Ileak\_max}$ = 10 µA + [number of IOs where V_{IN} is applied on the pad] x I_{lkg}(Max).
7. To sustain a voltage higher than MIN(V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{LCD}) +0.3 V, the internal Pull-up and Pull-Down resistors must be disabled.
8. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (~10% order).

1. Guaranteed by design, unless otherwise specified.
2. Refer to *Table 25: Embedded internal voltage reference*.
3. Guaranteed by characterization results.

6.3.21 Operational amplifiers characteristics

Table 73. OPAMP characteristics(1)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage(2)	-		1.8	-	3.6	V
CMIR	Common mode input range	-		0	-	V_{DDA}	V
VI_{OFFSET}	Input offset voltage	25 °C, No Load on output.		-	-	±1.5	mV
		All voltage/Temp.		-	-	±3	
ΔVI_{OFFSET}	Input offset voltage drift	Normal mode		-	±5	-	µV/°C
		Low-power mode		-	±10	-	
TRIMOFFSETP TRIMLPOFFSETP	Offset trim step at low common input voltage (0.1 x V_{DDA})	-		-	0.8	1.1	mV
TRIMOFFSETN TRIMLPOFFSETN	Offset trim step at high common input voltage (0.9 x V_{DDA})	-		-	1	1.35	
I_{LOAD}	Drive current	Normal mode	$V_{DDA} \geq 2$ V	-	-	500	µA
		Low-power mode		-	-	100	
I_{LOAD_PGA}	Drive current in PGA mode	Normal mode	$V_{DDA} \geq 2$ V	-	-	450	
		Low-power mode		-	-	50	
R_{LOAD}	Resistive load (connected to VSSA or to VDDA)	Normal mode	$V_{DDA} < 2$ V	4	-	-	kΩ
		Low-power mode		20	-	-	
R_{LOAD_PGA}	Resistive load in PGA mode (connected to VSSA or to V_{DDA})	Normal mode	$V_{DDA} < 2$ V	4.5	-	-	
		Low-power mode		40	-	-	
C_{LOAD}	Capacitive load	-		-	-	50	pF
CMRR	Common mode rejection ratio	Normal mode		-	-85	-	dB
		Low-power mode		-	-90	-	

Table 73. OPAMP characteristics(1) (continued)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
PSRR	Power supply rejection ratio	Normal mode	C_{LOAD} ≤ 50 pf, R_{LOAD} ≥ 4 kΩ DC	70	85	-	dB
		Low-power mode	C_{LOAD} ≤ 50 pf, R_{LOAD} ≥ 20 kΩ DC	72	90	-	
GBW	Gain Bandwidth Product	Normal mode	V_{DDA} ≥ 2.4 V (OPA_RANGE = 1)	550	1600	2200	kHz
		Low-power mode		100	420	600	
		Normal mode	V_{DDA} < 2.4 V (OPA_RANGE = 0)	250	700	950	
		Low-power mode		40	180	280	
SR(3)	Slew rate (from 10 and 90% of output voltage)	Normal mode	V_{DDA} ≥ 2.4 V	-	700	-	V/ms
		Low-power mode		-	180	-	
		Normal mode	V_{DDA} < 2.4 V	-	300	-	
		Low-power mode		-	80	-	
AO	Open loop gain	Normal mode		55	110	-	dB
		Low-power mode		45	110	-	
V_{OHSAT}(3)	High saturation voltage	Normal mode	I_{load} = max or R_{load} = min Input at V_{DDA}.	V_{DDA} - 100	-	-	mV
		Low-power mode		V_{DDA} - 50	-	-	
V_{OLSAT}(3)	Low saturation voltage	Normal mode	I_{load} = max or R_{load} = min Input at 0.	-	-	100	
		Low-power mode		-	-	50	
φ_m	Phase margin	Normal mode		-	74	-	°
		Low-power mode		-	66	-	
GM	Gain margin	Normal mode		-	13	-	dB
		Low-power mode		-	20	-	
t_{WAKEUP}	Wake up time from OFF state.	Normal mode	C_{LOAD} ≤ 50 pf, R_{LOAD} ≥ 4 kΩ follower configuration	-	5	10	µs
		Low-power mode	C_{LOAD} ≤ 50 pf, R_{LOAD} ≥ 20 kΩ follower configuration	-	10	30	
I_{bias}	OPAMP input bias current	Dedicated input (BGA132 only)		-	-	-(4)	nA
		General purpose input (all packages except BGA132)		-	-	-(4)	
PGA gain(3)	Non inverting gain value	-		-	2	-	-
				-	4	-	
				-	8	-	
				-	16	-	

USB characteristics

The STM32L476xx USB interface is fully compliant with the USB specification version 2.0 and is USB-IF certified (for Full-speed device operation).

Table 89. USB electrical characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDUSB}	USB transceiver operating voltage		3.0(1)	-	3.6	V
R_{PUI}	Embedded USB_DP pull-up value during idle		900	1250	1600	Ω
R_{PUR}	Embedded USB_DP pull-up value during reception		1400	2300	3200	
Z_{DRV}(2)	Output driver impedance(3)	Driving high and low	28	36	44	Ω

1. The STM32L476xx USB functionality is ensured down to 2.7 V but not the full USB electrical characteristics which are degraded in the 2.7-to-3.0 V voltage range.
2. Guaranteed by design.
3. No external termination series resistors are required on USB_DP (D+) and USB_DM (D-); the matching impedance is already included in the embedded driver.

CAN (controller area network) interface

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (CAN_TX and CAN_RX).

6.3.28 FSMC characteristics

Unless otherwise specified, the parameters given in *Table 90* to *Table 103* for the FMC interface are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage conditions summarized in *Table 22*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output characteristics.

Asynchronous waveforms and timings

Figure 37 through *Figure 40* represent asynchronous waveforms and *Table 90* through *Table 97* provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- AddressSetupTime = 0x1
- AddressHoldTime = 0x1
- DataSetupTime = 0x1 (except for asynchronous NWAIT mode, DataSetupTime = 0x5)
- BusTurnAroundDuration = 0x0

In all timing tables, the THCLK is the HCLK clock period.

Table 90. Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$2T_{HCLK}$-0.5	$2T_{HCLK}$+0.5	ns
$t_{v(NOE\_NE)}$	FMC_NEx low to FMC_NOE low	0	1	
$t_{w(NOE)}$	FMC_NOE low time	$2T_{HCLK}$-0.5	$2T_{HCLK}$+1	
$t_{h(NE\_NOE)}$	FMC_NOE high to FMC_NE high hold time	0	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	3.5	
$t_{h(A\_NOE)}$	Address hold time after FMC_NOE high	0	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	2	
$t_{h(BL\_NOE)}$	FMC_BL hold time after FMC_NOE high	0	-	
$t_{su(Data\_NE)}$	Data to FMC_NEx high setup time	T_{HCLK}-1	-	
$t_{su(Data\_NOE)}$	Data to FMC_NOEx high setup time	T_{HCLK}-0.5	-	
$t_{h(Data\_NOE)}$	Data hold time after FMC_NOE high	0	-	
$t_{h(Data\_NE)}$	Data hold time after FMC_NEx high	0	-	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	-	1	
$t_{w(NADV)}$	FMC_NADV low time	-	T_{HCLK}+0.5	

1. CL = 30 pF.
2. Guaranteed by characterization results.

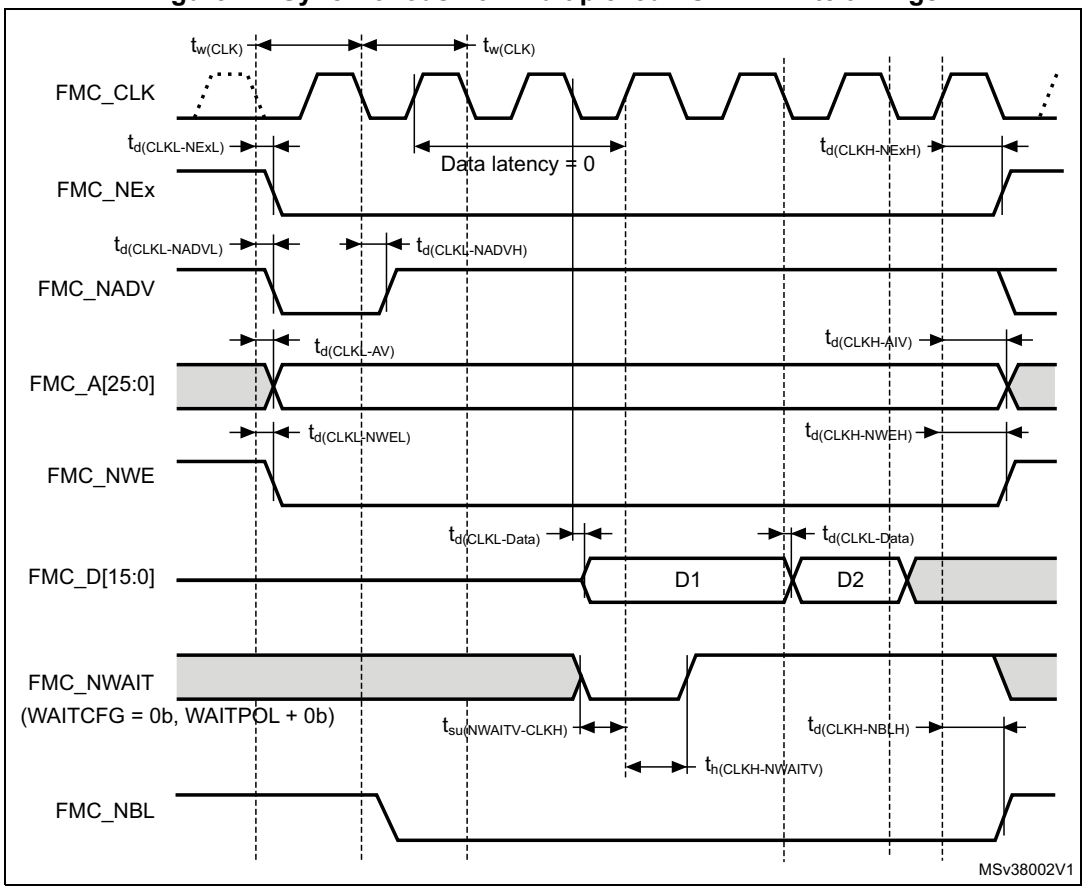
Table 91. Asynchronous non-multiplexed SRAM/PSRAM/NOR read-NWAIT timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$7T_{HCLK}$-0.5	$7T_{HCLK}$+0.5	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK}$-0.5	$5T_{HCLK}$+0.5	
$t_{w(NWAIT)}$	FMC_NWAIT low time	T_{HCLK}-0.5	-	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK}$+2	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}$	-	

1. CL = 30 pF.
2. Guaranteed by characterization results.

1. CL = 30 pF.
2. Guaranteed by characterization results.

Figure 44. Synchronous non-multiplexed PSRAM write timings



As applications do not commonly use the STM32L476xx at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 82 °C (measured according to JESD51-2), I_{DDmax} = 50 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V and maximum 8 I/Os used at the same time in output at low level with I_{OL} = 20 mA, V_{OL}= 1.3 V

P_{INTmax} = 50 mA × 3.5 V= 175 mW

P_{IOmax} = 20 × 8 mA × 0.4 V + 8 × 20 mA × 1.3 V = 272 mW

This gives: P_{INTmax} = 175 mW and P_{IOmax} = 272 mW:

P_{Dmax} = 175 + 272 = 447 mW

Using the values obtained in *Table 113* T_{Jmax} is calculated as follows:

– For LQFP64, 45 °C/W

T_{Jmax} = 82 °C + (45 °C/W × 447 mW) = 82 °C + 20.115 °C = 102.115 °C

This is within the range of the suffix 6 version parts (–40 < T_J < 105 °C) see *Section 8: Part numbering*.

In this case, parts must be ordered at least with the temperature range suffix 6 (see Part numbering).

Note: With this given P_{Dmax} we can find the T_{Amax} allowed for a given device temperature range (order code suffix 6 or 7).

Suffix 6: T_{Amax} = T_{Jmax} - (45°C/W × 447 mW) = 105-20.115 = 84.885 °C

Suffix 7: T_{Amax} = T_{Jmax} - (45°C/W × 447 mW) = 125-20.115 = 104.885 °C

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 100 °C (measured according to JESD51-2), I_{DDmax} = 20 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V

P_{INTmax} = 20 mA × 3.5 V= 70 mW

P_{IOmax} = 20 × 8 mA × 0.4 V = 64 mW

This gives: P_{INTmax} = 70 mW and P_{IOmax} = 64 mW:

P_{Dmax} = 70 + 64 = 134 mW

Thus: P_{Dmax} = 134 mW